

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant: Kie Y. Ahn et al.

Title: GATE OXIDES AND METHODS OF FORMING

Docket No.: 1303.021US1
Filed: August 30, 2001
Examiner: Walter Lindsay



Serial No.: 09/944,981
Due Date: June 18, 2004
Group Art Unit: 2812

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MS Amendment

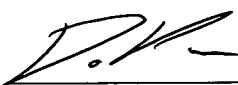
Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

We are transmitting herewith the following attached items (as indicated with an "X"):

- ☒ A return postcard.
- ☒ An Amendment and Response (11 Pages).
- ☒ A Communication Concerning Related Applications (3 pgs.).
- ☒ An Information Disclosure Statement (1 pg.), Form 1449 (12 pgs.), and copies of 222 cited documents.
- ☒ A check in the amount of \$180.00 to cover the fee for consideration of Information Disclosure Statement under 97(c).

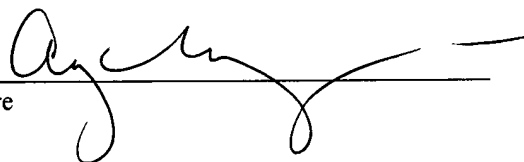
Please consider this a **PETITION FOR EXTENSION OF TIME** for sufficient number of months to enter these papers and please charge any additional fees or credit overpayment to Deposit Account No. 19-0743.

SCHWEGMAN, LUNDBERG, WOESSNER & KLUTH, P.A.
Customer Number 21186

By: 
Atty: David C. Peterson
Reg. No. 47,857

CERTIFICATE UNDER 37 CFR 1.8: The undersigned hereby certifies that this correspondence is being deposited with the United States Postal Service with sufficient postage as first class mail, in an envelope addressed to: MS Amendment, Commissioner for Patents, P.O. Box 1450, Alexandria, VA 22313-1450, on this 18th day of June, 2004.

Name Amy Moriarty

Signature 

SCHWEGMAN, LUNDBERG, WOESSNER & KLUTH, P.A.
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S/N 09/944,981

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Serial No.: 09/944,981

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Filed: August 30, 2001

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Title: CRYSTALLINE OR AMOPHOUS MEDIUM-K GATE OXIDES, Y2O3 AND GD2O3

COMMUNICATION CONCERNING RELATED APPLICATION(S)

MS Amendment

Commissioner for Patents

P.O. Box 1450

Alexandria, VA 22313-1450

Applicants would like to bring to the Examiner's attention the following related application(s) in the above-identified patent application:

<u>Serial/Patent No.</u>	<u>Filing Date</u>	<u>Attorney Docket</u>	<u>Title</u>
09/945535	August 30, 2001	1303.026US1	HIGHLY RELIABLE AMORPHOUS HIGH-K GATE OXIDE ZrO2
10/028643	December 20, 2001	1303.030US1	LOW-TEMPERATURE GROWN HIGH QUALITY ULTRA-THIN CoTiO3 GATE DIELECTRICS
10/052983	January 17, 2002	1303.031US1	HIGHLY RELIABLE AMORPHOUS HIGH-k GATE DIELECTRIC ZrOxNy
10/027315 6740581	December 20, 2001	1303.033US1	LOW-TEMPERATURE GROWN HIGH-QUALITY ULTRA-THIN PRASEODYMIUM GATE DIELECTRICS
10/099194	March 13, 2002	1303.044US1	EVAPORATION OF Y-Si-O FILMS FOR MEDIUM-k DIELECTRICS
10/081439	February 20, 2002	1303.046US1	EVAPORATED LaAlO3 FILMS FOR GATE DIELECTRICS
10/137499	May 2, 2002	1303.050US1	ATOMIC LAYER-DEPOSITED LaAlO3 FILMS FOR GATE DIELECTRICS

COMMUNICATION CONCERNING RELATED APPLICATIONS

Serial Number: 09/944,981

Filing Date: August 30, 2001

Title: CRYSTALLINE OR AMOPHOUS MEDIUM-K GATE OXIDES, Y2O3 AND GD2O3

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10/163481	June 5, 2002	1303.056US1	ATOMIC LAYER-DEPOSITED HfAlO ₃ FILMS FOR GATE DIELECTRICS
10/163686	June 5, 2002	1303.059US1	Pr ₂ O ₃ -BASED La-oxide GATE DIELECTRICS
10/219870	August 15, 2002	1303.069US1	LANTHANIDE DOPED TiO _x DIELECTRIC FILMS BY PLASMA OXIDATION
10/219878	August 15, 2002	1303.070US1	LANTHANIDE DOPED TiO _x DIELECTRIC FILMS
10/229903	August 28, 2002	1303.078US1	ATOMIC LAYER DEPOSITED HfSiON DIELECTRIC FILMS
10/233309	August 29, 2002	1303.079US1	ATOMIC LAYER DEPOSITED LANTHANIDE DOPED TiO _x DIELECTRIC FILMS
10/309583	December 4, 2002	1303.082US1	ATOMIC LAYER DEPOSITED ZR-SN- TI-O FILMS USING TiI ₄
10/309935	December 4, 2002	1303.083US1	ATOMIC LAYER DEPOSITED Zr-Sn- Ti-O FILMS
10/379470	March 4, 2003	1303.090US1	ATOMIC LAYER DEPOSITED DIELECTRIC LAYERS
10/403734	March 31, 2003	1303.092US1	ATOMIC LAYER DEPOSITED ZrAl _x O _y DIELECTRIC LAYERS
10/420307	April 22, 2003	1303.097US1	ATOMIC LAYER DEPOSITED ZrTiO ₄ FILMS
10/602323	June 24, 2003	1303.101US1	LANTHANIDE OXIDE / HAFNIUM OXIDE DIELECTRIC LAYERS
10/602315	June 24, 2003	1303.107US1	LANTHANIDE OXIDE / HAFNIUM OXIDE DIELECTRICS

COMMUNICATION CONCERNING RELATED APPLICATIONS

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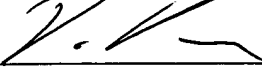
10/765619	January 27, 2004	1303.033US2	LOW-TEMPERATURE GROWN HIGH-QUALITY ULTRA-THIN PRASEODYMIUM GATE DIELECTRICS
10/768597	January 30, 2004	1303.033US3	LOW-TEMPERATURE GROWN HIGH-QUALITY ULTRA-THIN PRASEODYMIUM GATE DIELECTRICS
10/789044	February 27, 2004	1303.070US2	LANTHANIDE DOPED TiOx DIELECTRIC FILMS
Unknown	June 9, 2004	1303.031US2	HIGHLY RELIABLE AMORPHOUS HIGH-k GATE DIELECTRIC ZrOxNy
09/779959	February 9, 2001		
09/838335	April 20, 2001		
09/881408	June 13, 2001		
09/908767	July 18, 2001		

Respectfully submitted,

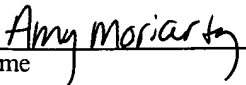
KIE Y. AHN ET AL.

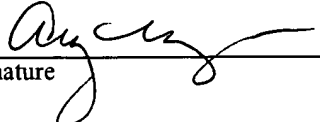
By Applicants' Representatives,

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Date 6-18-04 By 
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Reg. No. 47,857

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Name


Signature